

<b>SANYO</b>	No.4243A	<b>2SJ281</b>
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

**Absolute Maximum Ratings at Ta = 25°C**

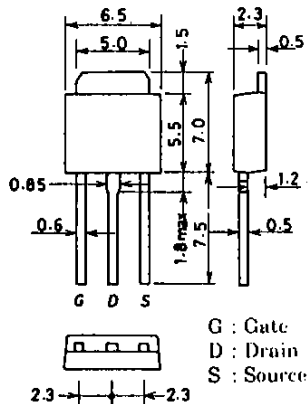
Drain to Source Voltage	$V_{DSS}$		-250	V
Gate to Source Voltage	$V_{GSS}$		±30	V
Drain Current(DC)	$I_D$		-3	A
Drain Current(Pulse)	$I_{DP}$	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-12	A
Allowable Power Dissipation	$P_D$		1.0	W
		$T_c = 25^\circ C$	30	W
Channel Temperature	$T_{ch}$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-250			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	±30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -250V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 25V, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.5		-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -1.5A$	1.5	2.5		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -1.5A, V_{GS} = -10V$		1.5	2.0	Ω
Input Capacitance	$C_{iss}$	$V_{DS} = -20V, f = 1MHz$		420		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -20V, f = 1MHz$		100		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -20V, f = 1MHz$		40		pF

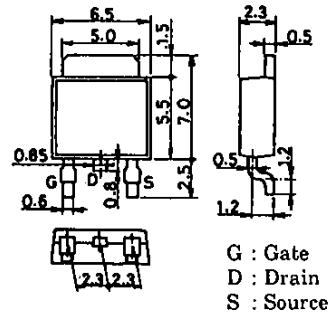
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**Package Dimensions 2083A**  
(unit : mm)



SANYO: TP

**Package Dimensions 2092A**  
(unit : mm)



G : Gate  
D : Drain  
S : Source

SANYO: TP-FA

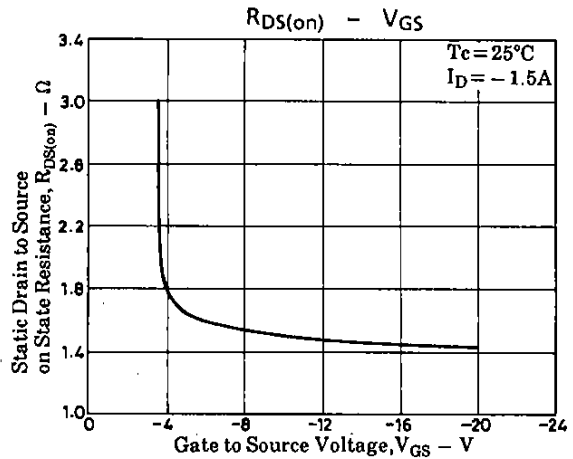
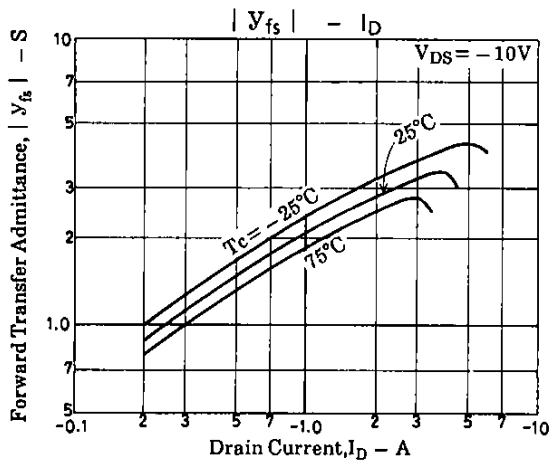
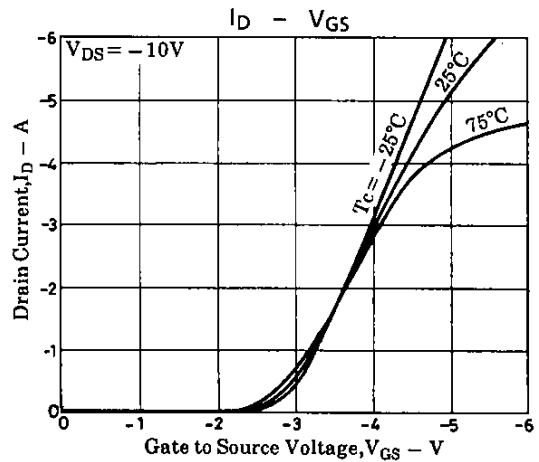
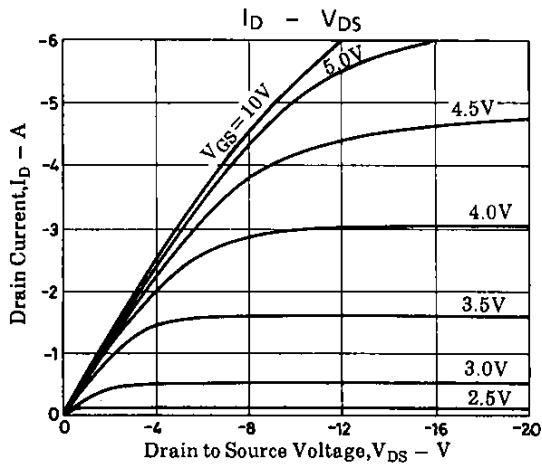
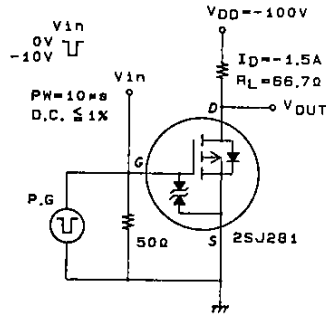
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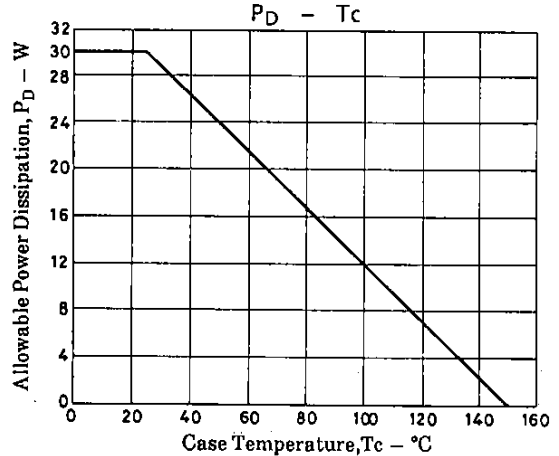
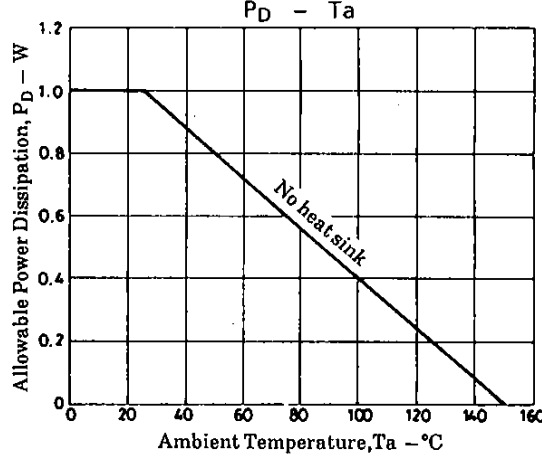
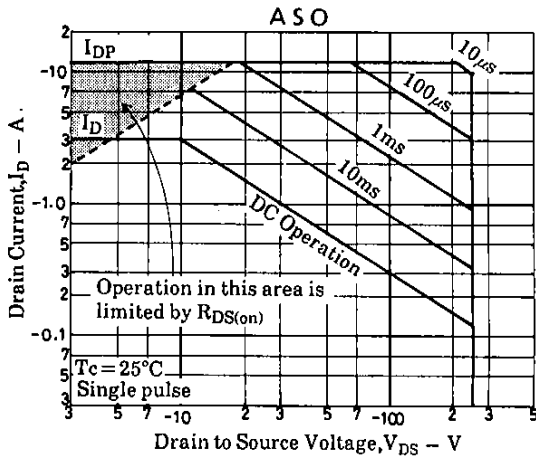
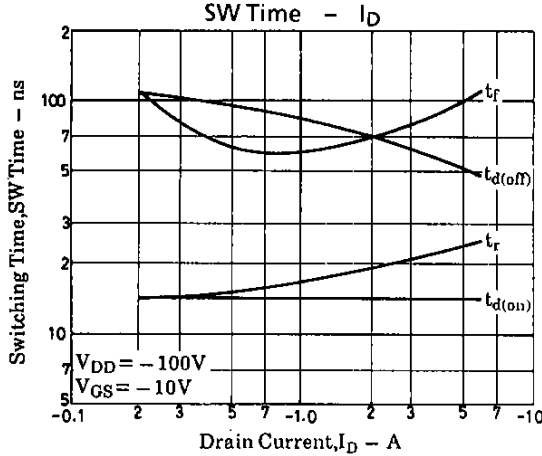
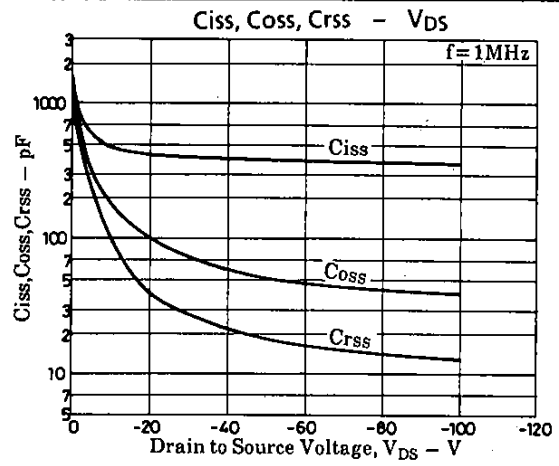
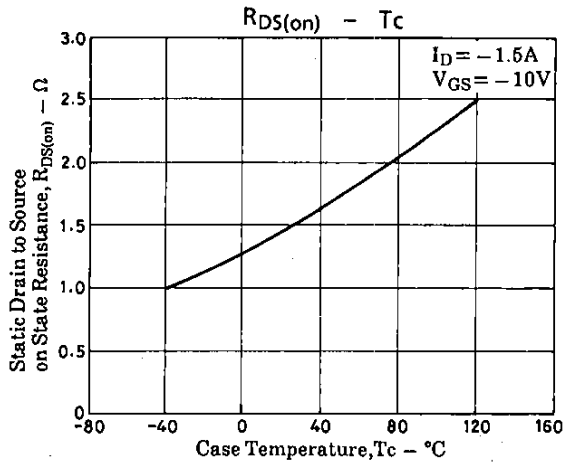
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			min	typ	max	unit
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		14		ns
Rise Time	$t_r$	"		18		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		75		ns
Fall Time	$t_f$	"		65		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -3A, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit





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